

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

2SA1483

HIGH FREQUENCY AMPLIFIER APPLICATIONS
 VIDEO AMPLIFIER APPLICATIONS
 HIGH SPEED SWITCHING APPLICATIONS

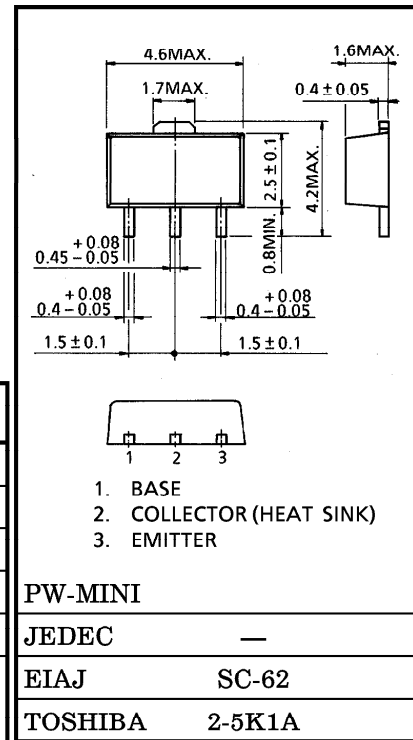
- High Transition Frequency : $f_T = 200\text{MHz}$ (Typ.)
- Low Collector Output Capacitance : $C_{ob} = 3.5\text{pF}$ (Typ.)
- Complementary to 2SC3803

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-60	V
Collector-Emitter Voltage	V_{CEO}	-45	V
Emitter-Base Voltage	V_{EBO}	-5	V
Continuous Collector Current	I_C	-200	mA
Continuous Base Current	I_B	-50	mA
Collector Power Dissipation	P_C	500	mW
	P_C^*	1000	
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^\circ\text{C}$

* : Mounted on ceramic substrate (250mm²×0.8t)

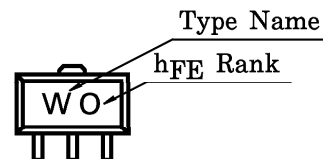
Unit in mm



PW-MINI	
JEDEC	—
EIAJ	SC-62
TOSHIBA	2-5K1A

Weight : 0.05g

Marking



961001EAA2

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● The information contained herein is subject to change without notice.

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT				
Collector Cut-off Current	I_{CBO}	$V_{CB} = -45V, I_E = 0$	—	—	-0.1	μA				
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5V, I_C = 0$	—	—	-0.1	μA				
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE} = -1V, I_C = -10mA$	40	—	240					
	$h_{FE(2)}$	$V_{CE} = -3V, I_C = -200mA$	20	—	—					
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -100mA, I_B = -10mA$	—	—	-0.3	V				
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -100mA, I_B = -10mA$	—	—	-1.0	V				
Transition Frequency	f_T	$V_{CE} = -10V, I_C = -10mA$	100	200	—	MHz				
Input Impedance (Real Part)	$Re(h_{ie})$	$V_{CE} = -10V, I_E = 10mA,$ $f = 200MHz$	—	—	120	Ω				
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$	—	3.5	5	pF				
Switching Time	Turn-on Time	t_{on}					—	40	—	ns
	Storage Time	t_{stg}					—	250	—	
	Fall Time	t_f					—	30	—	

Note : $h_{FE(1)}$ Classification R : 40~80, O : 70~140, Y : 120~240

